



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

## SOT-363 Plastic-Encapsulate Diodes

**BAV199DW** Multi-Chip DIODES

### FEATURES

Power dissipation

$P_{CM}$ : 0.2 W ( $T_{amb}=25^{\circ}C$ )

Collector current

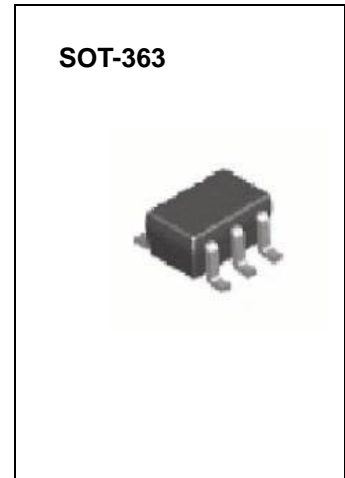
$I_F$  : 200 mA

Collector-base voltage

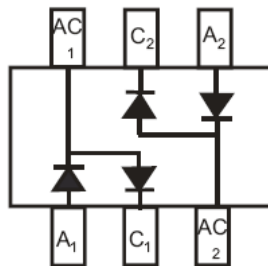
$V_R$  : 85 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



### MARKING:K52

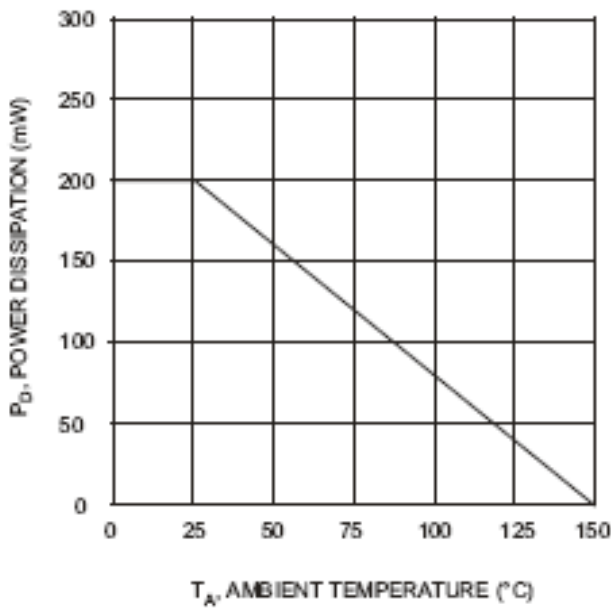


### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

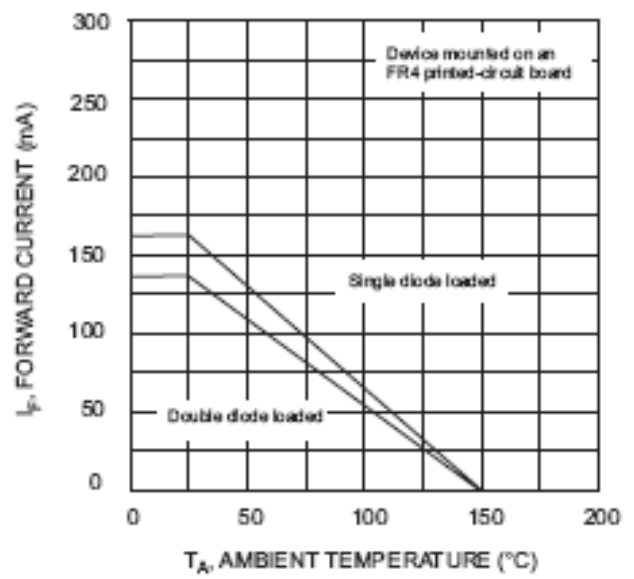
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$	85			V
Reverse voltage leakage current	$I_R$	$V_R=75V$			5	nA
Forward voltage	$V_F$	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$			0.9 1.0 1.1 1.25	V
Junction capacitance	$C_j$	$V_R=0V$ $f=1MHz$		2		pF
Reverses recovery time	$t_{rr}$	$I_F=I_R=10mA$ $I_{rr}=0.1I_R$ $R_L=100\Omega$			3	nS

# Typical Characteristics

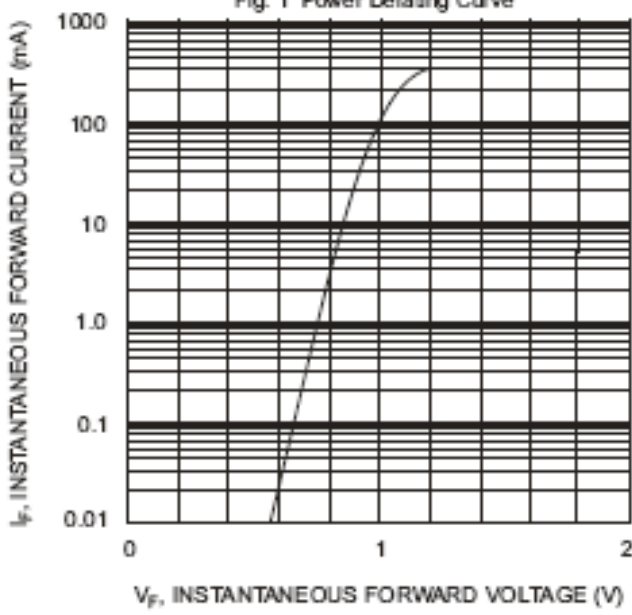
# BAV199DW



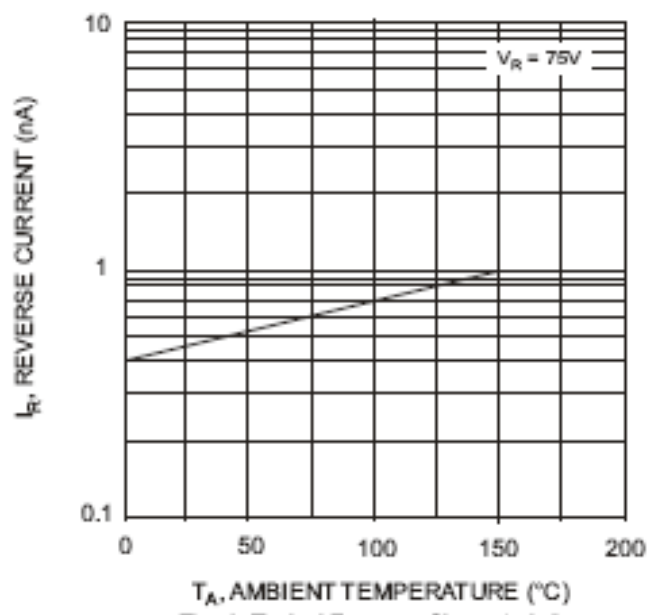
$T_A$ , AMBIENT TEMPERATURE (°C)  
Fig. 1 Power Derating Curve



$T_A$ , AMBIENT TEMPERATURE (°C)  
Fig. 2 Current Derating Curve



$V_F$ , INSTANTANEOUS FORWARD VOLTAGE (V)  
Fig. 3 Typical Forward Characteristics



$T_A$ , AMBIENT TEMPERATURE (°C)  
Fig. 4 Typical Reverse Characteristics